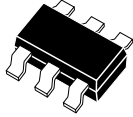


CMXD2004
SUPER-MINI
TRIPLE ISOLATED
SURFACE MOUNT
HIGH VOLTAGE
SWITCHING DIODE



SOT-26 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD2004 type contains three (3) Isolated High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring high voltage capability. Marking code is X04.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

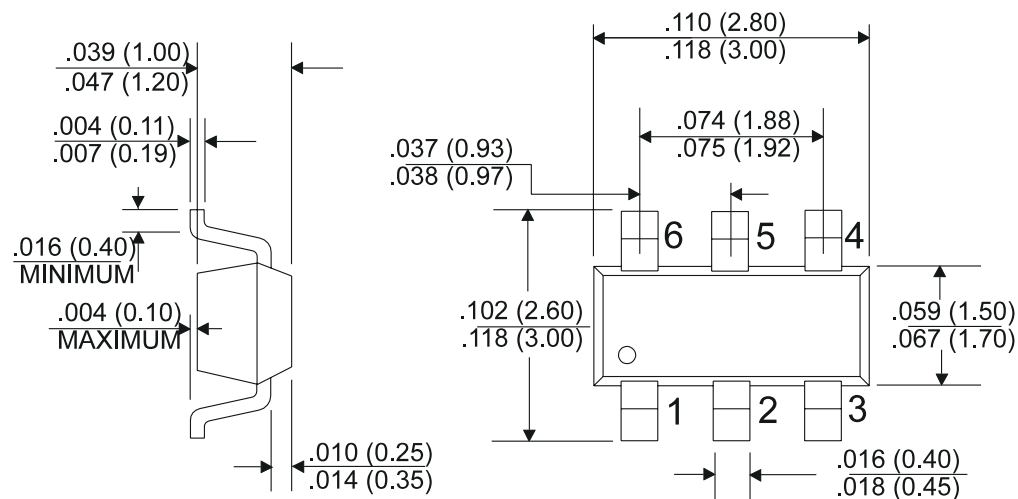
	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, $t_p=1$ ms	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1$ s	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage	T_J, T_{stg}	65 to +150	$^\circ\text{C}$
Junction Temperature	Θ_{JA}	357	$^\circ\text{C/W}$
Thermal Resistance			

ELECTRICAL CHARACTERISTICS PER DIODE ($T_A=25^\circ\text{C}$ unless otherwise noted)

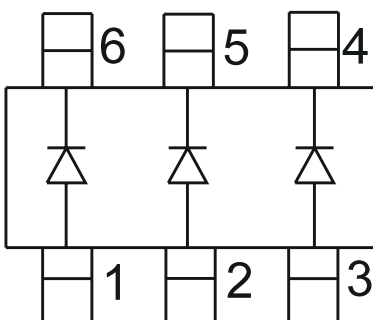
SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	$V_R=240\text{V}$		100	nA
I_R	$V_R=240\text{V}, T_A=150^\circ\text{C}$		100	μA
BV_R	$I_R=100\mu\text{A}$	300		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1\text{ MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, \text{Rec. To } 3.0\text{mA}, R_L=100\Omega$		50	ns

R1 (14-Sept 2000)

TOP VIEW



Pin Configuration

**Lead Code**

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1